

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

MAEDA et al

Serial No.:

Filed: March 15, 2001

For: FILM-FORMING SURFACE REFORMING METHOD AND
SEMICONDUCTOR DEVICE MANUFACTURING METHOD

PRELIMINARY AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

Please amend the captioned application as follows:

IN THE CLAIMS:

Please rewrite claims 12 as follows:

12. (Amended) A semiconductor device manufacturing method according to claim 6, wherein the insulating film is a silicon-containing insulating film which is formed by a thermal chemical vapor deposition employing a reaction gas that contains an ozone-containing gas and a tetraethylorthosilicate.

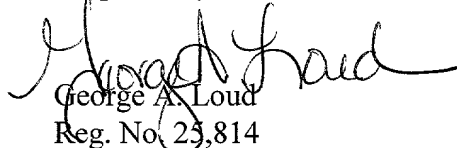
Please add the following new claims:

--13. A semiconductor device manufacturing method according to claim 7, wherein the insulating film is a silicon-containing insulating film which is formed by a thermal chemical vapor deposition employing a reaction gas that contains an ozone-containing gas and a tetraethylorthosilicate.

14. A semiconductor device manufacturing method according to claim 8, wherein the insulating film is a silicon-containing insulating film which is formed by a thermal chemical vapor deposition employing a reaction gas that contains an ozone-containing gas and a tetraethylorthosilicate.

15. A semiconductor device manufacturing method according to claim 11, wherein the insulating film is a silicon-containing insulating film which is formed by a thermal chemical vapor deposition employing a reaction gas that contains an ozone-containing gas and a tetraethylorthosilicate.--

Respectfully submitted,


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Dated: March 15, 2001

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12. (Amended) A semiconductor device manufacturing method according to claim 6 [any one of claims 6, 7, 8, and 11], wherein the insulating film is a silicon-containing insulating film which is formed by a thermal chemical vapor deposition employing a reaction gas that contains an ozone-containing gas and a tetraethylorthosilicate.